### What is claimed is:

1. An organic transistor, comprising:

an organic layer inserted between a semi-conducting layer and a source or drain electrode,

wherein the organic layer includes at least one compound represented by Chemical Formula I.

Formula I

2. The organic transistor of claim 1, wherein the organic layer is further inserted between the semi-conducting layer and the source and drain electrodes.

- 3. The organic transistor of claim 1, further comprising:
- a substrate;
- a gate electrode disposed in the substrate;
- an insulating layer disposed over the gate electrode and the substrate;
- the semi-conducting layer disposed on the insulating layer; and
- the source and drain electrodes disposed over the semi-conducting layer and the insulating layer.
- 4. The organic transistor of claim 1, further comprising:
- a substrate;
- a gate electrode disposed in the substrate;
- an insulating layer disposed over the gate electrode and the substrate;
- the source and drain electrodes disposed on the insulating layer; and
- the semi-conducting layer disposed over the insulating layer and the source and drain
- electrodes.
- 5. The organic transistor of claim 1, further comprising:
- a substrate;
- the source and drain electrodes disposed on the substrate;
- the semi-conducting layer disposed over the substrate and the source and drain
- electrodes;
- an insulating layer disposed on the semi-conducting layer; and
- a gate electrode disposed in the insulating layer.

6. The organic transistor of claim 1, further comprising:

a substrate;

the semi-conducting layer disposed in the substrate;

the source and drain electrodes disposed in the semi-conducting layer;

an insulating layer disposed on the semi-conducting layer and the source and drain

electrodes; and

a gate electrode disposed in the insulating layer.

- 7. The organic transistor of claim 1, wherein the source or drain electrode include aluminum, silver, gold, neodymium, palladium, platinum, gold, or alloys of the foregoing metals.
- 8. The organic transistor of claim 1, wherein the source or drain electrode include composite materials including aluminum or silver.

9. The organic transistor of claim 1, wherein the chemical compound I includes one of the following compounds Ia to Ig.

Formula la

Formula Ic

Formula Ie

Formula Ib

Formula Id

Formula If

Formula Ig

# 10. A method for manufacturing an organic transistor, comprising:

inserting an organic layer between a semi-conducting layer and a source or drain electrode to improve electric contact between the semi-conducting layer and the source or drain electrode,

wherein the organic layer includes at least one compound represented by Chemical Formula I.

Formula I

11. The method of claim 10, further comprising inserting the organic layer between the semi-conducing layer and the source and drain electrodes.

### 12. The method of claim 10, further comprising:

forming a gate electrode in a substrate;

forming an insulating layer over the gate electrode and the substrate;

forming the semi-conducting layer on the insulating layer; and

forming the source and drain electrodes over the semi-conducting layer and the insulating layer.

### 13. The method of claim 10, further comprising:

forming a gate electrode in a substrate;

forming an insulating layer over the gate electrode and the substrate;

forming the source and drain electrodes on the insulating layer; and

forming the semi-conducting layer over the insulating layer and the source and drain electrodes.

#### 14. The method of claim 10, further comprising:

forming the source and drain electrodes on a substrate;

forming the semi-conducting layer over the substrate and the source and drain electrodes;

forming an insulating layer on the semi-conducting layer; and

forming a gate electrode in the insulating layer.

15. The method of claim 10, further comprising:

forming the semi-conducting layer in a substrate;

forming the source and drain electrodes in the semi-conducting layer;

forming an insulating layer on the semi-conducting layer and the source and drain electrodes; and

forming a gate electrode in the insulating layer.

16. The method of claim 10, wherein the chemical compound I includes one of the following compounds Ia to Ig.

Formula Ia

Formula Ic

Formula Ib

Formula Id

Formula Ig

- 17. The method of claim 10, further comprising forming the source and drain electrodes as one of aluminum, silver, gold, neodymium, palladium, platinum, gold, and alloys of the foregoing metals.
- 18. The method of claim 10, further comprising forming the source and drain electrodes with composite materials including aluminum or silver.

# 19. An organic transistor, comprising:

an organic layer including at least one compound represented by Chemical Formula I.

Formula I